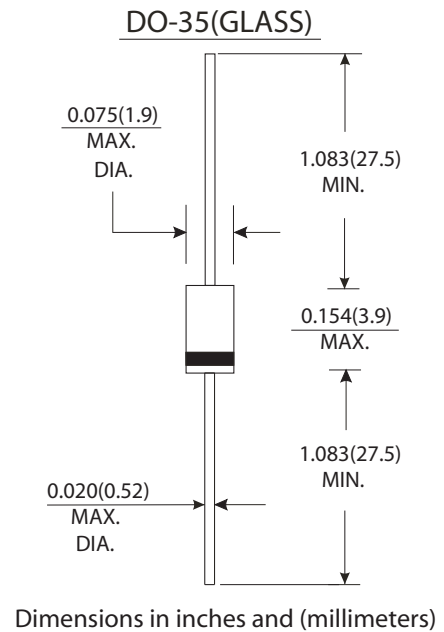


Features

- Silicon epitaxial planar diode
- Fast switching diodes
- 500mW power dissipation
- This diode is also available in the Mini-MELF case with the type designation LL4148

Mechanical Data

- Case: DO-35 glass case
- Polarity: Color band denotes cathode end
- Weight: Approx. 0.13 gram



Maximum Ratings And Electrical Characteristics

(Ratings at 25 °C ambient temperature unless otherwise specified)

Type	Type Differentiation	Ordering Code	Remarks
BAW75	$V_{RRM} = 35 \text{ V}$	BAW75±TAP	Ammopack

Absolute Maximum Ratings

$T_j = 25 \text{ °C}$

Parameter	Test Conditions	Type	Symbol	Value	Unit
Repetitive peak reverse voltage			V_{RRM}	35	V
Reverse voltage			V_R	25	V
Peak forward surge current	$t_p=1 \text{ s}$		I_{FSM}	2000	mA
Repetitive peak forward current			I_{FRM}	450	mA
Forward current			I_F	300	mA
Average forward current	$V_R=0$		I_{FAV}	150	mA
Power dissipation	$l=4 \text{ mm}, T_L=45 \text{ °C}$		P_V	440	mW
	$l=4 \text{ mm}, T_L=25 \text{ °C}$		P_V	500	mW
Junction temperature			T_j	200	°C
Storage temperature range			T_{stg}	±65...+200	°C

Maximum Thermal Resistance

$T_j = 25 \text{ °C}$

Parameter	Test Conditions	Symbol	Value	Unit
Junction ambient	$l=4 \text{ mm}, T_L=\text{constant}$	R_{thJA}	350	K/W

Features

Electrical Characteristics

$T_j = 25\text{ }^\circ\text{C}$

Parameter	Test Conditions	Type	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F=30\text{mA}$		V_F			1	V
Reverse current	$V_R=25\text{ V}$		I_R			100	nA
	$V_R=25\text{ V}, T_j=150\text{ }^\circ\text{C}$		I_R			100	A
Breakdown voltage	$I_R=5\text{ A}, t_p/T=0.01, t_p=0.3\text{ms}$		$V_{(BR)}$	35			V
Diode capacitance	$V_R=0, f=1\text{MHz}, V_{HF}=50\text{mV}$		C_D			4	pF
Reverse recovery time	$I_F=I_R=10\text{mA}, i_R=1\text{mA}$		t_{rr}			4	ns
	$I_F=10\text{mA}, V_R=6\text{V}, i_R=1\text{mA}, R_L=100$		t_{rr}			2	ns